

STPS30M60C

Power Schottky rectifier

Features

- High current capability
- Avalanche rated
- Low forward voltage drop
- High frequency operation

Description

The STPS30M60C is a dual diode Schottky rectifier, suited for high frequency switch mode power supply.

Packaged in TO-220AB, I²PAK and D²PAK, this device is intended to be used in notebook, game station and desktop adapters, providing in these applications a good efficiency at both low and high load.

Table 1. Device summary

Symbol	Value
I _{F(AV)}	2 x 15 A
V _{RRM}	60 V
V _F (typ)	0.380 V
T _j (max)	150 °C

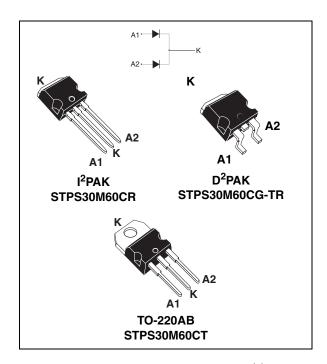
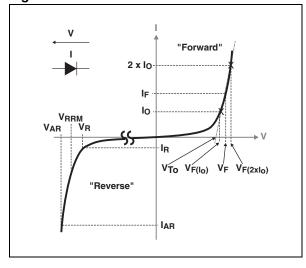


Figure 1. Electrical characteristics^(a)



V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in *Figure 12*. V_{AR} and I_{AR} are pulse measurements (t_p < 1 μs). V_R, I_R, V_{RRM} and V_F, are static characteristics

November 2011 Doc ID 022020 Rev 1 1/10

Characteristics STPS30M60C

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode, at T_{amb} = 25 °C unless otherwise specified)

Symbol	Parameter			Value	Unit	
V_{RRM}	Repetitive peak reverse voltage			60	V	
I _{F(RMS)}	Forward rms current				60	Α
	Average forward current, $\delta = 0.5$		T _c = 135 °C	Per diode	15	Α
I _{F(AV)}			T _c = 135 °C	Per device	30	A
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms sine-wave}$			400	Α	
P _{ARM} ⁽¹⁾	Repetitive peak avalanche power $T_j = 25$ °C, $t_p = 1$ µs		17600	W		
V _{ARM} ⁽²⁾	Maximum repetitive peak avalanche voltage	t _p < 1 μs, T _j < 150 °C, I _{AR} < 66 A		80	٧	
V _{ARM} ⁽²⁾	Maximum single-pulse peak avalanche voltage	t _p < 1 μs, T _j < 150 °C, I _{AR} < 66 A		80	V	
T _{stg}	Storage temperature range	age temperature range			-65 to +175	°C
T _j	Maximum operating junction temperature ⁽³⁾			150	ç	

For temperature or pulse time duration deratings, please refer to Figure 4 and 5. More details regarding the
avalanche energy measurements and diode validation in the avalanche are provided in the application
notes AN1768 and AN2025.

Table 3. Thermal parameters

Symbol	Parameter	Value	Unit	
D	Junction to case	er diode	1.3	°C/W
R _{th(j-c)}	total	0.73	C/VV	
R _{th(c)}	Coupling		0.15	°C/W

When the two diodes 1 and 2 are used simultaneously:

$$\Delta T_i$$
(diode 1) = P(diode 1) x R_{th(i-c)}(Per diode) + P(diode 2) x R_{th(c)}

^{2.} See Figure 12

^{3.} $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

STPS30M60C Characteristics

Table 4.	Static electrical	characteristics ((per diode)
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Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
ı (1)	IR ⁽¹⁾ Reverse leakage current	T _j = 25 °C	V - V	-	20	80	μΑ
'R`´		T _j = 125 °C	$V_R = V_{RRM}$	-	15	50	mA
		T _j = 25 °C	I _F = 7.5 A	-	0.475	0.515	
V _F ⁽²⁾ Forward voltage drop	T _j = 125 °C	IF = 7.5 A	-	0.380	0.425	V	
	Porward voltage drop	T _j = 25 °C	Ι – 15 Λ	-	0.540	0.590	V
		T _j = 125 °C	I _F = 15 A	-	0.470	0.530	

- 1. Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$
- 2. Pulse test: $t_p = 380 \mu s$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

 $P = 0.385 \text{ x } I_{F(AV)} + 0.0097 \text{ x } I_{F}^{2}_{(RMS)}$

Figure 2. Average forward power dissipation Figure 3. versus average forward current (per diode)

Average forward current versus ambient temperature (δ = 0.5, per diode)

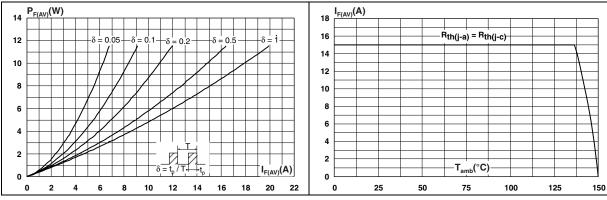
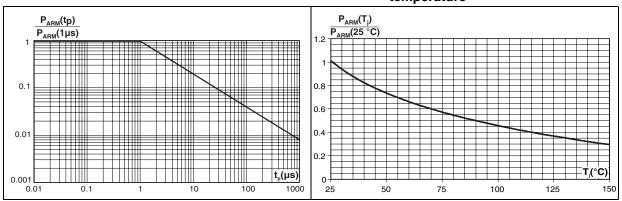


Figure 4. Normalized avalanche power derating versus pulse duration

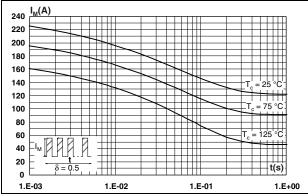
Figure 5. Normalized avalanche power derating versus junction temperature



Characteristics STPS30M60C

Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

Figure 7. Relative thermal impedance junction to case versus pulse duration



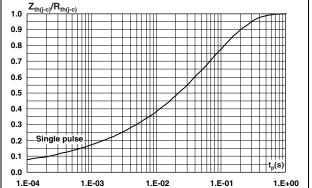
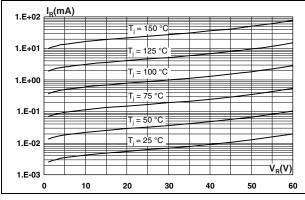


Figure 8. Reverse leakage current versus reverse voltage applied (typical values, per diode)

Figure 9. Junction capacitance versus reverse voltage applied (typical values, per diode)



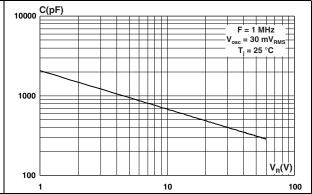
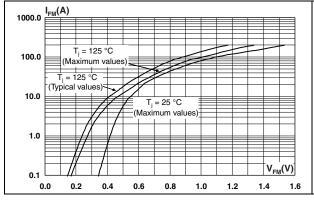
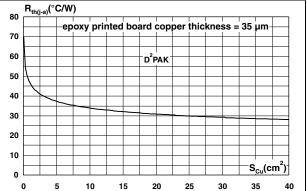


Figure 10. Forward voltage drop versus forward current (per diode)

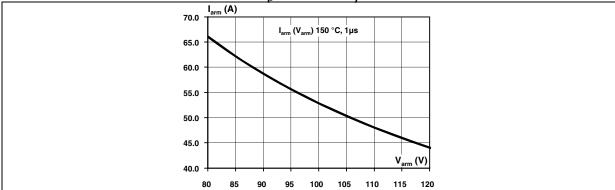
Figure 11. Thermal resistance junction to ambient versus copper surface under tab





STPS30M60C Characteristics

Figure 12. Reverse safe operating area ($t_p < 1 \mu s$ and $T_j < 150 °C$)

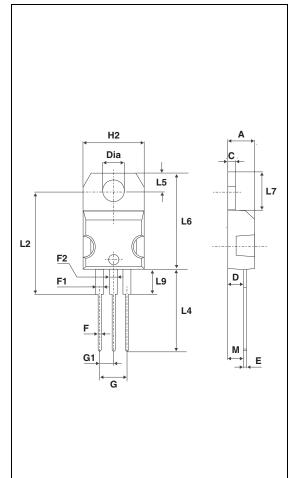


2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N⋅m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 5. TO-220AB dimensions

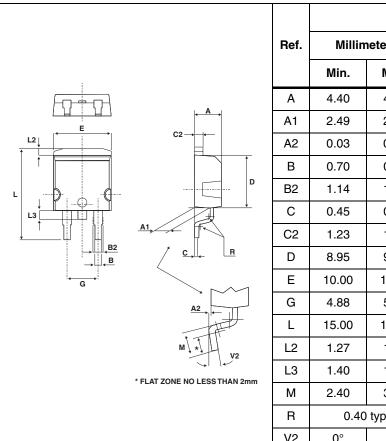


	Dimensions			
Ref.	Millin	neters	Inc	hes
	Min.	Max.	Min.	Max.
Α	4.40	4.60	0.173	0.181
С	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
Е	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4	Тур.	0.645 Typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
М	2.6	Тур.	0.102	2 Typ.
Dia.	3.75	3.85	0.147	0.151

6/10 Doc ID 022020 Rev 1

STPS30M60C Package information

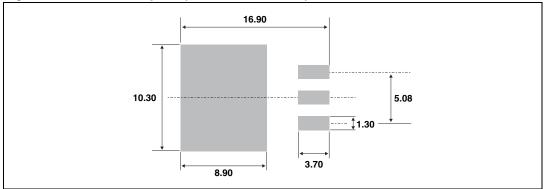
Table 6. D²PAK dimensions



Millimeters Inches Max. Min. Max. 4.60 0.173 0.181 2.69 0.098 0.106 0.23 0.001 0.009 0.93 0.027 0.037 1.70 0.045 0.067 0.60 0.017 0.024 1.36 0.048 0.054 9.35 0.352 0.368 10.40 0.393 0.409 5.28 0.192 0.208 15.85 0.590 0.624 1.40 0.050 0.055 1.75 0.055 0.069 3.20 0.094 0.126 0.40 typ. 0.016 typ. V2 0° 0°

Dimensions

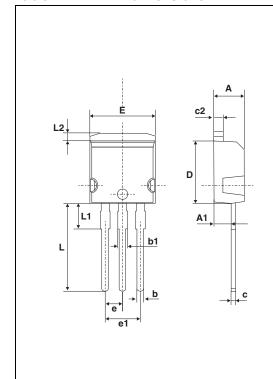
Figure 13. D²PAK footprint (dimensions in mm)



57

Package information STPS30M60C

Table 7. I²PAK dimensions



	Dimensions					
Ref.	Millim	neters	Inches			
	Min.	Max.	Min.	Max.		
Α	4.40	4.60	0.173	0.181		
A1	2.40	2.72	0.094	0.107		
b	0.61	0.88	0.024	0.035		
b1	1.14	1.70	0.044	0.067		
С	0.49	0.70	0.019	0.028		
c2	1.23	1.32	0.048	0.052		
D	8.95	9.35	0.352	0.368		
е	2.40	2.70	0.094	0.106		
e1	4.95	5.15	0.195	0.203		
E	10	10.40	0.394	0.409		
L	13	14	0.512	0.551		
L1	3.50	3.93	0.138	0.155		
L2	1.27	1.40	0.050	0.055		

3 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS30M60CT	STPS30M60CT	TO-220AB	2.20 g	50	Tube
STPS30M60CR	STPS30M60CR	I ² PAK	1.49 g	50	Tube
STPS30M60CG-TR	STPS30M60CG	D ² PAK	1.48 g	1000	Tape and reel

4 Revision history

Table 9.Revision history

Date	Revision	Changes
02-Nov-2011	1	First issue.

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